

# NTMD2P01R2

## Power MOSFET -2.3 Amps, -16 Volts

### Dual SOIC-8 Package

#### Features

- High Efficiency Components in a Single SOIC-8 Package
- High Density Power MOSFET with Low  $R_{DS(on)}$
- Logic Level Gate Drive
- SOIC-8 Surface Mount Package, Mounting Information for SOIC-8 Package Provided
- Pb-Free Packages are Available

#### Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular and Cordless Telephones

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-16	V
Gate-to-Source Voltage - Continuous	$V_{GS}$	$\pm 10$	V
Thermal Resistance - Junction-to-Ambient (Note 1)	$R_{\theta JA}$	175	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	0.71	W
Continuous Drain Current @ $T_A = 25^\circ\text{C}$	$I_D$	-2.3	A
Continuous Drain Current @ $T_A = 100^\circ\text{C}$	$I_D$	-1.45	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-9.0	A
Thermal Resistance - Junction-to-Ambient (Note 2)	$R_{\theta JA}$	105	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	1.19	W
Continuous Drain Current @ $T_A = 25^\circ\text{C}$	$I_D$	-2.97	A
Continuous Drain Current @ $T_A = 100^\circ\text{C}$	$I_D$	-1.88	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-12	A
Thermal Resistance - Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	2.0	W
Continuous Drain Current @ $T_A = 25^\circ\text{C}$	$I_D$	-3.85	A
Continuous Drain Current @ $T_A = 100^\circ\text{C}$	$I_D$	-2.43	A
Pulsed Drain Current (Note 4)	$I_{DM}$	-15	A
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = -16\text{ Vdc}$ , $V_{GS} = -4.5\text{ Vdc}$ , Peak $I_L = -5.0\text{ Apk}$ , $L = 28\text{ mH}$ , $R_G = 25\ \Omega$ )	$E_{AS}$	350	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

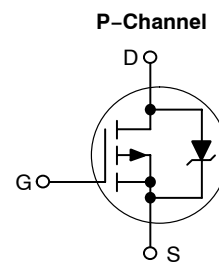
1. Minimum FR-4 or G-10 PCB, Steady State.
2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz Cu 0.06" thick single sided), Steady State.
3. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz Cu 0.06" thick single sided),  $t \leq 10$  seconds.
4. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2%.



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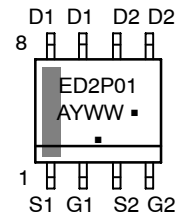
$V_{DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
-16 V	100 m $\Omega$ @ -4.5 V	-2.3 A



#### MARKING DIAGRAM\* AND PIN ASSIGNMENT



SOIC-8  
SUFFIX NB  
CASE 751  
STYLE 11



ED2P01 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*For additional marking information, refer to Application Note AND8002/D.

#### ORDERING INFORMATION

Device	Package	Shipping†
NTMD2P01R2	SOIC-8	2500/Tape & Reel
NTMD2P01R2G	SOIC-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

# NTMD2P01R2

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Positive)	V <sub>(BR)DSS</sub>	-16 -	- -12.7	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 25°C) (V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	I <sub>DSS</sub>	- -	- -	-1.0 -10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = -10 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	-100	nAdc
Gate-Body Leakage Current (V <sub>GS</sub> = +10 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	100	nAdc

### ON CHARACTERISTICS

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	-0.5 -	-0.90 2.5	-1.5 -	Vdc mV/°C
Static Drain-to-Source On-State Resistance (V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -2.4 Adc) (V <sub>GS</sub> = -2.7 Vdc, I <sub>D</sub> = -1.2 Adc) (V <sub>GS</sub> = -2.5 Vdc, I <sub>D</sub> = -1.2 Adc)	R <sub>DS(on)</sub>	- - -	0.070 0.100 0.110	0.100 0.130 0.150	Ω
Forward Transconductance (V <sub>DS</sub> = -10 Vdc, I <sub>D</sub> = -1.2 Adc)	g <sub>FS</sub>	-	4.2	-	Mhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	-	540	750	pF
Output Capacitance		C <sub>oss</sub>	-	215	325	
Reverse Transfer Capacitance		C <sub>rss</sub>	-	100	175	

### SWITCHING CHARACTERISTICS (Notes 6 and 7)

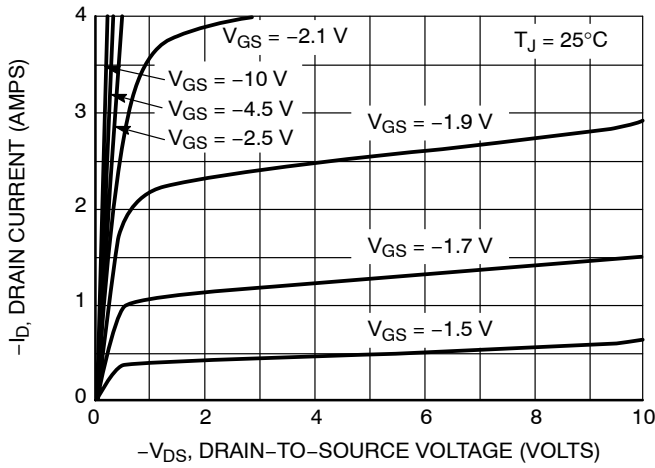
Turn-On Delay Time	(V <sub>DD</sub> = -10 Vdc, I <sub>D</sub> = -2.4 Adc, V <sub>GS</sub> = -4.5 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	10	20	ns
Rise Time		t <sub>r</sub>	-	35	65	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	33	60	
Fall Time		t <sub>f</sub>	-	29	55	
Turn-On Delay Time	(V <sub>DD</sub> = -10 Vdc, I <sub>D</sub> = -1.2 Adc, V <sub>GS</sub> = -2.7 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	15	-	ns
Rise Time		t <sub>r</sub>	-	40	-	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	35	-	
Fall Time		t <sub>f</sub>	-	35	-	
Total Gate Charge	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -2.4 Adc)	Q <sub>tot</sub>	-	10	18	nC
Gate-Source Charge		Q <sub>gs</sub>	-	1.5	-	
Gate-Drain Charge		Q <sub>gd</sub>	-	5.0	-	

### BODY-DRAIN DIODE RATINGS (Note 6)

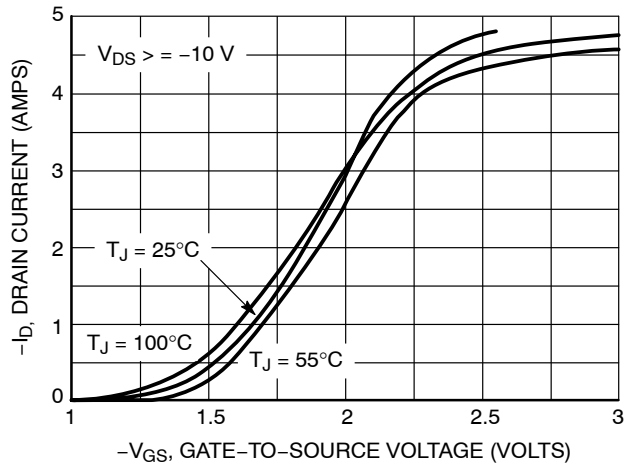
Diode Forward On-Voltage	(I <sub>S</sub> = -2.4 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = -2.4 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	- -	-0.88 -0.75	-1.0 -	Vdc
Reverse Recovery Time	(I <sub>S</sub> = -2.4 Adc, V <sub>GS</sub> = 0 Vdc, di <sub>S</sub> /dt = 100 A/μs)	t <sub>rr</sub>	-	37	-	ns
		t <sub>a</sub>	-	16	-	
		t <sub>b</sub>	-	21	-	
Reverse Recovery Stored Charge		Q <sub>RR</sub>	-	0.025	-	μC

5. Handling precautions to protect against electrostatic discharge is mandatory.
6. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.
7. Switching characteristics are independent of operating junction temperature.

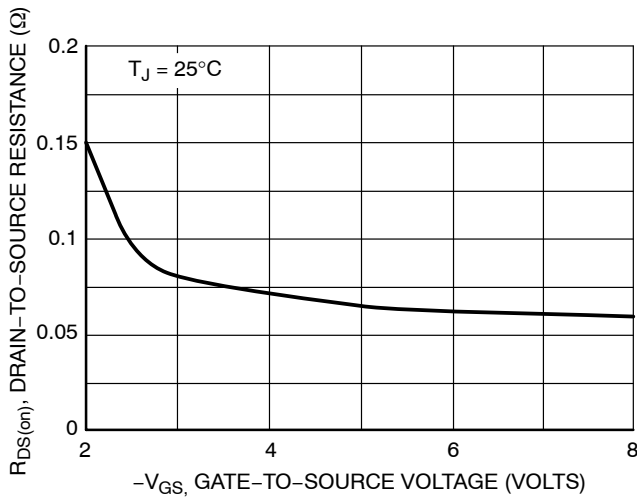
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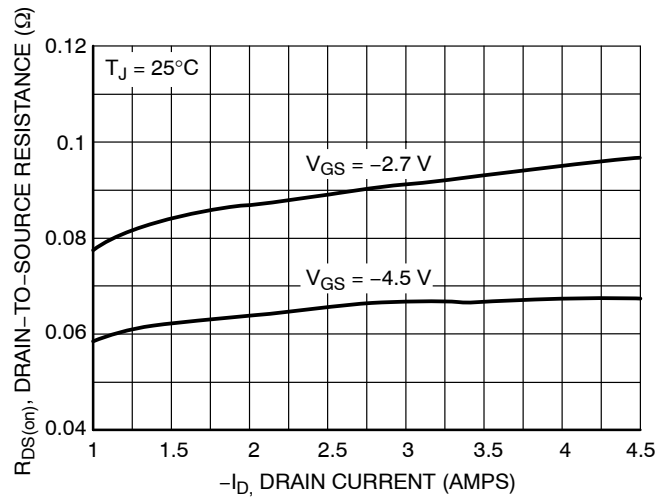
**Figure 1. On-Region Characteristics.**



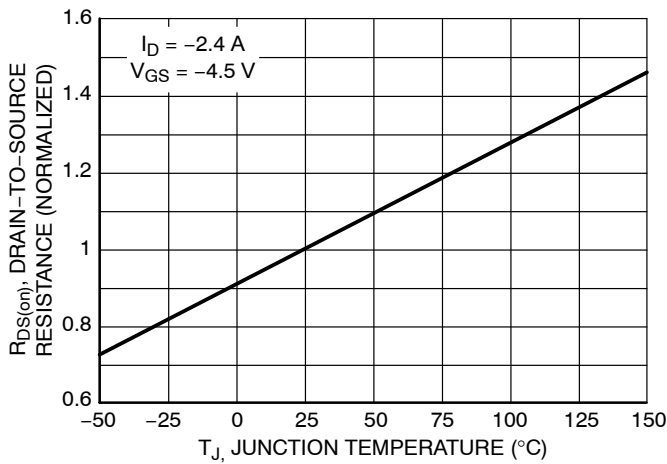
**Figure 2. Transfer Characteristics.**



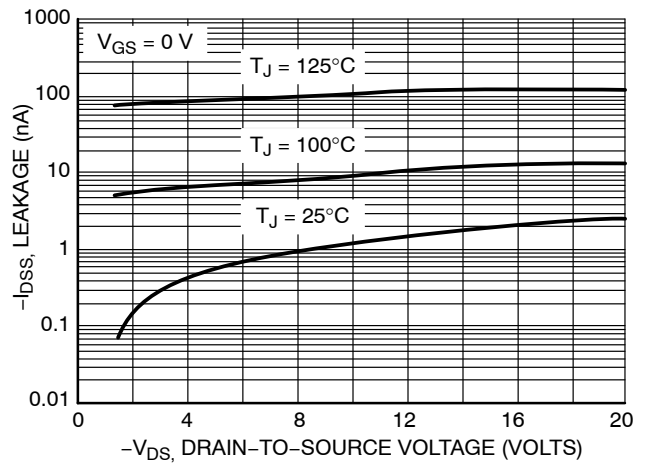
**Figure 3. On-Resistance vs. Gate-to-Source Voltage.**



**Figure 4. On-Resistance vs. Drain Current and Gate Voltage.**



**Figure 5. On-Resistance Variation with Temperature.**



**Figure 6. Drain-to-Source Leakage Current vs. Voltage.**

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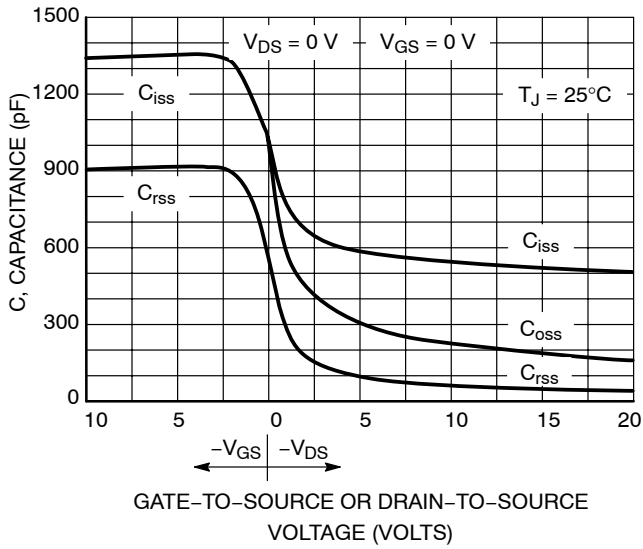


Figure 7. Capacitance Variation

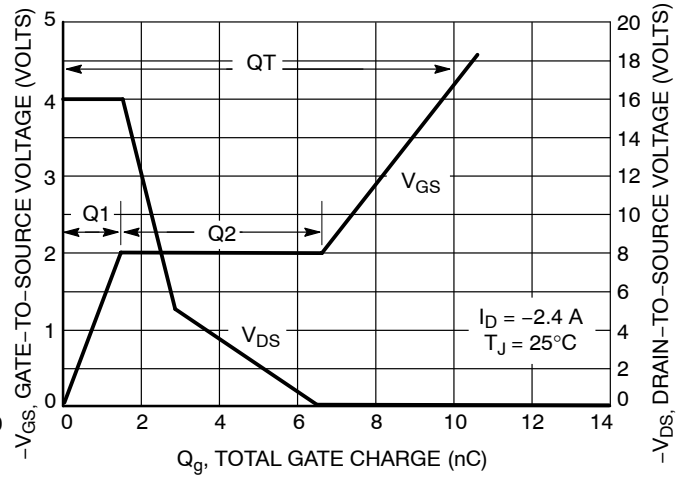


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

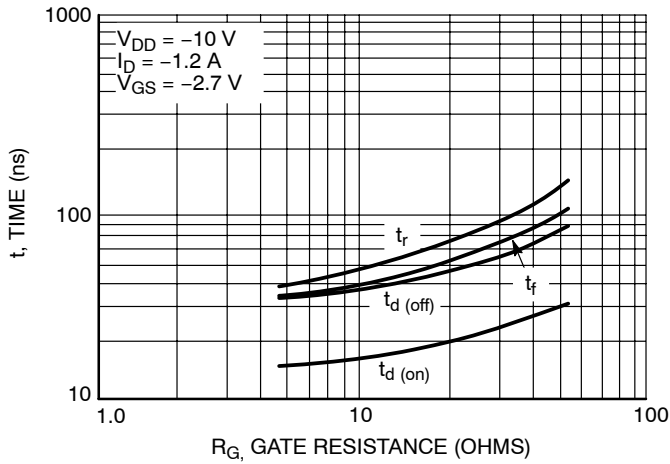


Figure 9. Resistive Switching Time Variation versus Gate Resistance

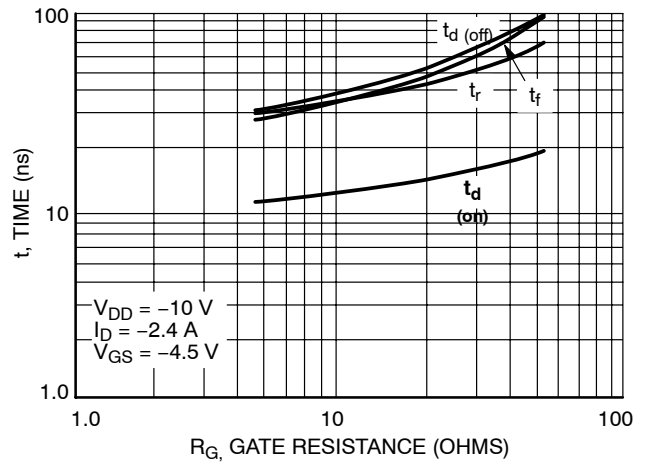


Figure 10. Resistive Switching Time Variation versus Gate Resistance

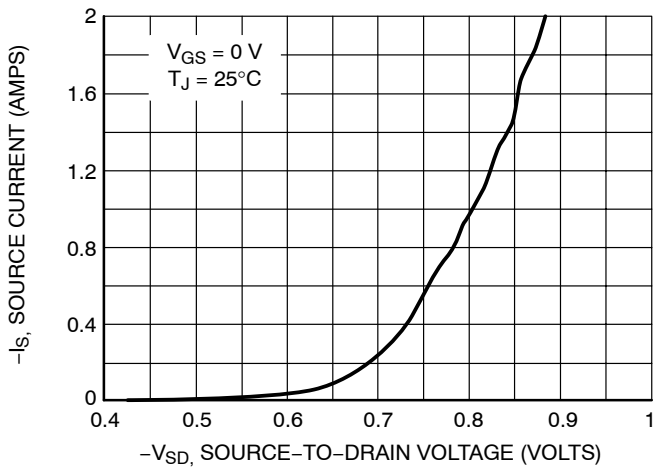


Figure 11. Diode Forward Voltage versus Current

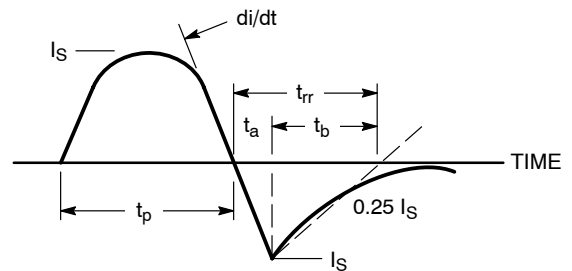


Figure 12. Diode Reverse Recovery Waveform

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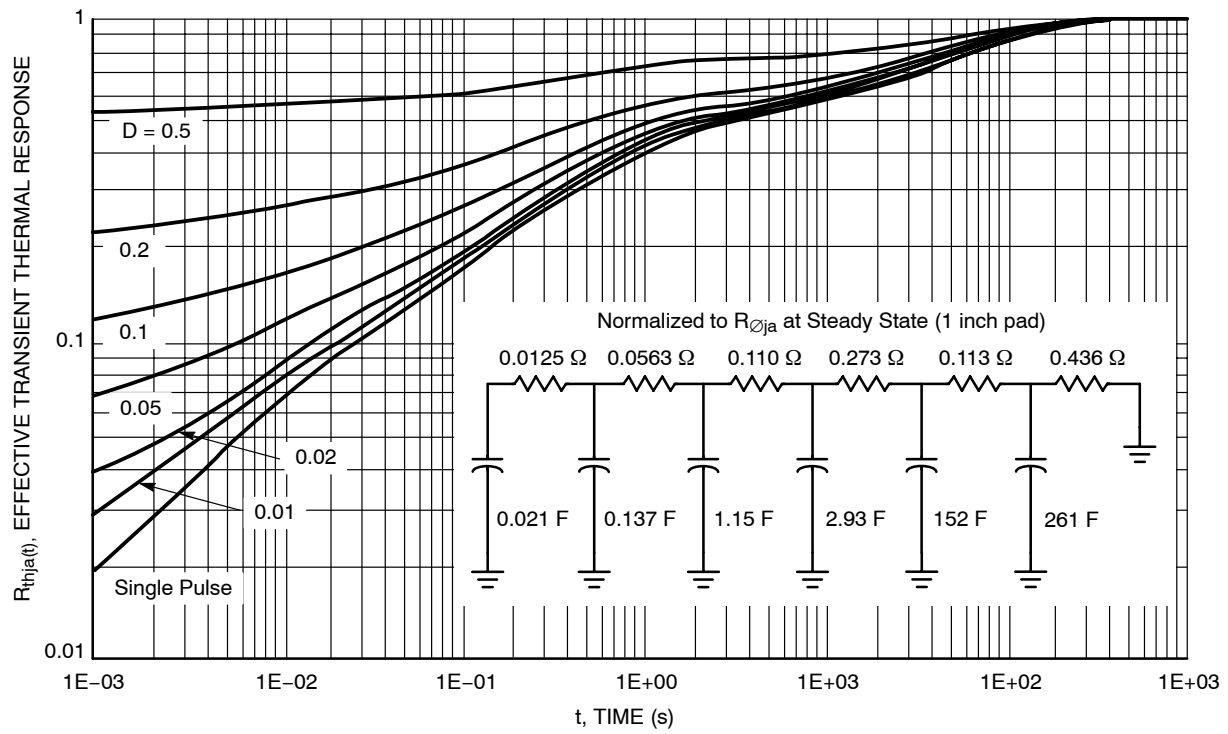
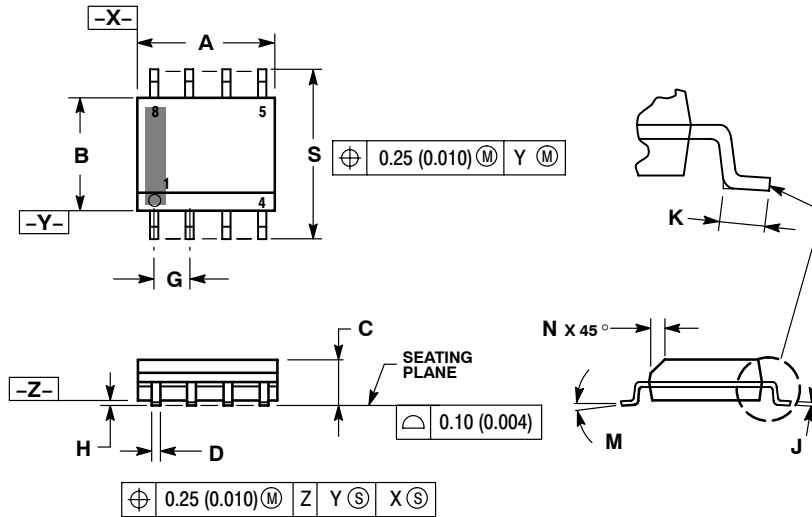


Figure 13. FET Thermal Response

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## PACKAGE DIMENSIONS

SOIC-8 NB  
CASE 751-07  
ISSUE AG

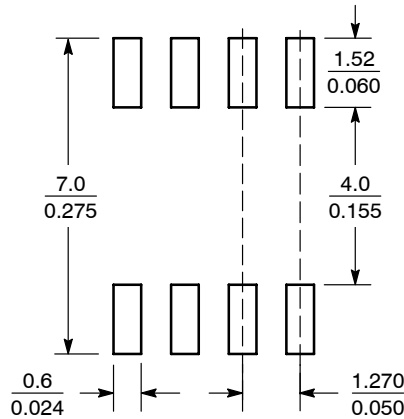


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

### SOLDERING FOOTPRINT\*



SCALE 6:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### STYLE 11:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

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